## **BECE206L - Analog Circuits**

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Professor

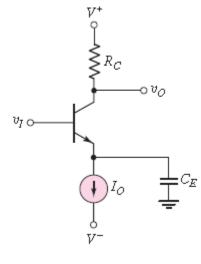
School of Electronics Engineering (SENSE)

#### Module 3

# MOSFET Active Biasing and Differential Amplifiers (6)

Introduction to Current Mirror – Basic, Wilson and Cascode Current Mirror, MOSFET Basic Differential Pair, Large Signal and Small Signal Analysis of Differential Amplifier, Differential Amplifier with active load.

### Introduction



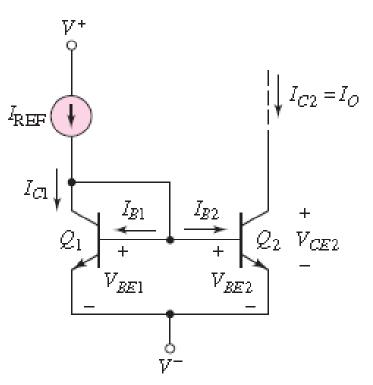
- Why is constant current source used for biasing in ICs?
  - resistor-intensive circuit would necessitate a large chip area
  - Hence, voltage divider biasing require relatively large area on IC
  - Also resistor biasing needs coupling capacitors in μF range, which is difficult to fabricate on an IC

## **Bipolar Transistor current sources**

- Types of circuits to produce constant current
   I<sub>o</sub>:
  - Two transistor current source
  - Three transistor current source
  - Widlar current source
  - Wilson Current source
  - Cascode current source

### **Two-Transistor current source**

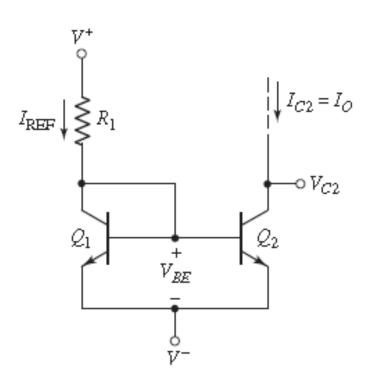
- Also called as Current mirror
- Use two matched or identical transistors-Q<sub>1</sub> & Q<sub>2</sub>
  - Operating at same temperature
  - Base and emitter terminals are tied together
  - B-E voltage is same in both transistors
- Transistor Q<sub>1</sub> is used as diode
- When supply is ON,
  - $V_{BE1}$  is established and  $I_{REF}$  flows
  - $V_{\rm BE2}$  is also same and turns ON  $Q_2$
  - Generating load current I<sub>o</sub>
  - I<sub>o</sub>: used to bias a transistor circuit



#### Two-transistor current source with resistor

- Current source can be replaced with resistor
- Then,

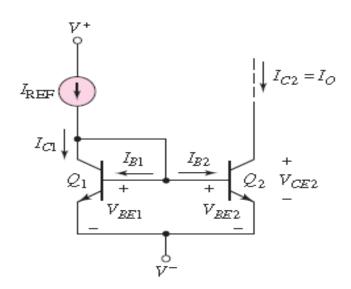
$$I_{\text{REF}} = \frac{V^+ - V_{BE} - V^-}{R_1}$$



## **Current relationships**

Since V<sub>BF</sub> is same in both the devices,

$$I_{B1} = I_{B2} \text{ and } I_{C1} = I_{C2}.$$



Transistor  $Q_2$  is assumed to be biased in the forward-active region. If we sum the currents at the collector node of  $Q_1$ , we have

$$I_{REF} = I_{C1} + I_{B1} + I_{B2} = I_{C1} + 2I_{B2}$$

Replacing  $I_{C1}$  by  $I_{C2}$  and noting that  $I_{B2} = I_{C2}/\beta$ ,

$$I_{\text{REF}} = I_{C2} + 2\frac{I_{C2}}{\beta} = I_{C2} \left(1 + \frac{2}{\beta}\right)$$

#### The output current is then

$$I_{C2} = I_O = \frac{I_{REF}}{1 + \frac{2}{\beta}}$$

assuming  $V_A$  is infinite

## **MOSFET Active Biasing**

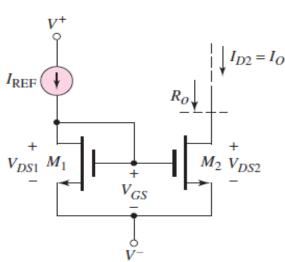
#### Outline

- Introduction to Current Mirror
- A Basic Current Mirror
- Wilson Current Mirror
- <sup>↑</sup> Cascode Current Mirror

#### **MOSFET Current Mirror**

- Biasing in the integrated by circuits is contant current sources using
- The constant DC current generated at one location will be replicated in other locations for biasing various amplifier stages through a process known as "Current Steering".
- The bias currents of various stages track eachother in case of changes in power supply voltage or in temperature.

#### **Basic MOSFET Current Mirror**



$$I_{REF} = K_{n1}(V_{GS} - V_{TN1})^2$$

Solving for  $V_{GS}$  yields

$$V_{GS} = V_{TN1} + \sqrt{\frac{I_{REF}}{K_{n1}}}$$

$$I_O = K_{n2}(V_{GS} - V_{TN2})^2$$

$$I_O = K_{n2} \left[ \sqrt{\frac{I_{\text{REF}}}{K_{n1}} + V_{TN1} - V_{TN2}} \right]^2$$

If  $M_1$  and  $M_2$  are identical transistors, then  $V_{TN1} = V_{TN2}$  and  $K_{n1} = K_{n2}$ ,

 $I_O = I_{\mathrm{REF}}$ 

If the transistors are matched except for the aspect ratios, we find

$$I_O = \frac{(W/L)_2}{(W/L)_1} \cdot I_{\text{REF}}$$

### **Effect of Output Resistance**

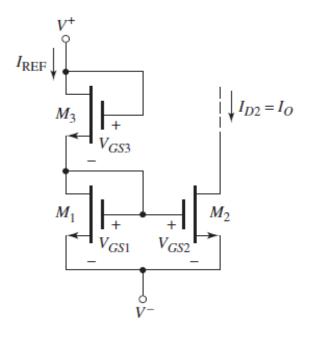
Taking into account the finite output resistance of the transistors, we can write the load and reference currents as

$$I_O = K_{n2}(V_{GS} - V_{TN2})^2 (1 + \lambda_2 V_{DS2})$$

$$I_{REF} = K_{n1}(V_{GS} - V_{TN1})^2 (1 + \lambda_1 V_{DS1})$$

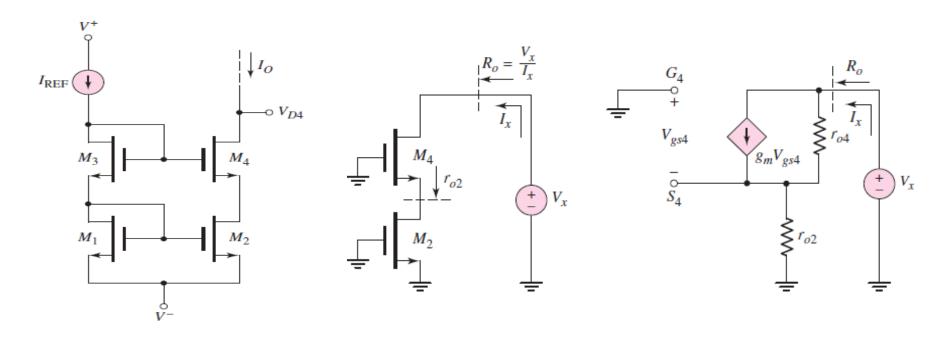
Replacing Resistor with M3

$$\frac{I_O}{I_{REF}} = \frac{(W/L)_2}{(W/L)_1} \cdot \frac{(1 + \lambda V_{DS2})}{(1 + \lambda V_{DS1})}$$



#### Cascode Current Mirror

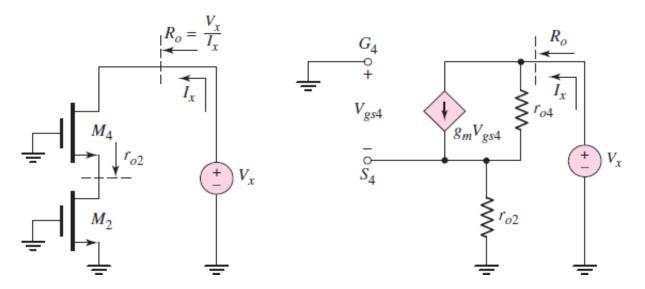
In MOSFET current-source circuits, the output resistance is a measure of the stability with respect to changes in the output voltage. This output resistance can be increased by modifying the circuit, which is a **cascode current mirror**.



Assuming all transistors are identical,

 $I_O = I_{REF}$ 

is a constant, the gate voltages to M1 and M3, and hence to M2 and M4, are constant. This is equivalent to an ac short circuit.



The small-signal resistance looking into the drain of M2 is rO2.

Writing a KCL equation, at the output node,

$$I_{x} = g_{m}V_{gs4} + \frac{V_{x} - (-V_{gs4})}{r_{o4}}$$

$$V_{gs4} = -I_{x}r_{o2}$$

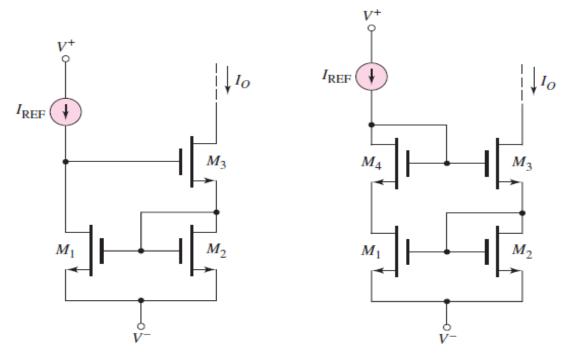
$$I_{x} + \frac{r_{o2}}{r_{o4}}I_{x} + g_{m}r_{o2}I_{x} = \frac{V_{x}}{r_{o4}}$$

The output resistance is then

$$R_o = \frac{V_x}{I_x} = r_{o4} + r_{o2}(1 + g_m r_{o4})$$

Normally,  $g_m r_{o4} \gg 1$ , which implies that the output resistance of this cascode configuration is much larger than that of the basic two-transistor current source.

#### Wilson Current Mirror



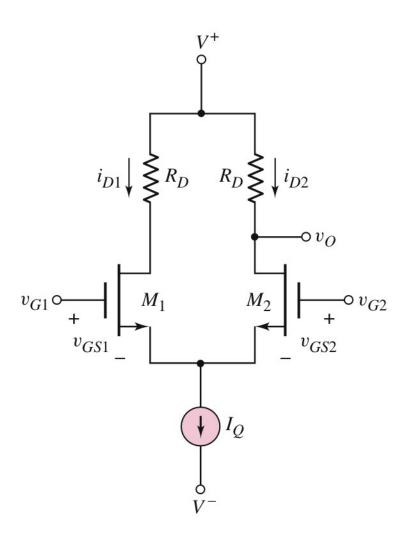
- Note that the VDS values of M1 and M2 are not equal. Since  $\lambda$  is not zero, the ratio IO/IREF is slightly different from the aspect ratios.
- <sup>^</sup> This problem is solved in the modified Wilson Current Source
  - For a constant reference current, the drain-to-source voltages of M1, M2, and M4 are held constant.
  - The primary advantage of these circuits is the increase in output resistance, which further stabilizes the load current.

#### In this chapter, we will:

- Describe the characteristics and terminology of the ideal differential amplifier.
- Describe the characteristics of and analyze:
  - the basic FET differential amplifier.
  - BJT and FET differential amplifiers with active loads.

 Analyze the frequency response of the differential amplifier.

## **MOSFET Differential Pair**



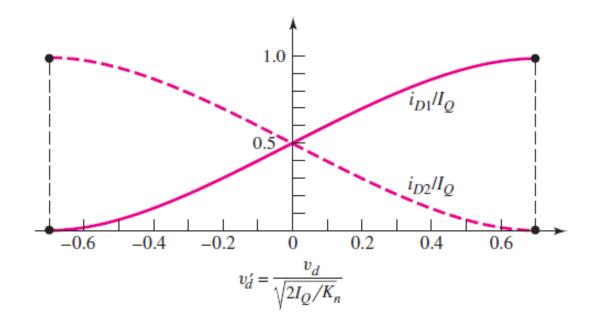
## Refer class notes

The normalized drain currents are

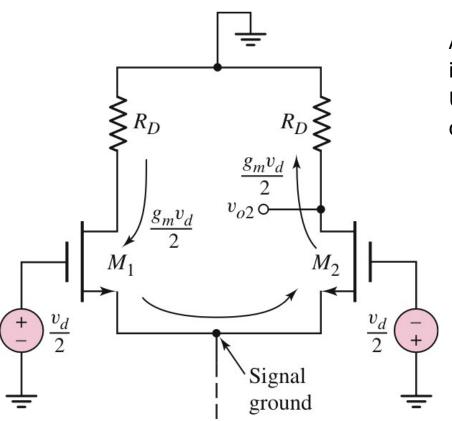
$$\frac{i_{D1}}{I_{Q}} = \frac{1}{2} + \sqrt{\frac{K_{n}}{2I_{Q}}} \cdot v_{d} \sqrt{1 - \left(\frac{K_{n}}{2I_{Q}}\right) v_{d}^{2}}$$

and

$$\frac{i_{D2}}{I_{Q}} = \frac{1}{2} - \sqrt{\frac{K_{n}}{2I_{Q}}} \cdot v_{d} \sqrt{1 - \left(\frac{K_{n}}{2I_{Q}}\right) v_{d}^{2}}$$



## Differential mode gain



Assume that the output resistance looking into the current source is infinite.

Using this equivalent circuit, the one sided output voltage, at M<sub>2</sub> is given as,

$$v_{o2} \equiv v_o = + \left(\frac{g_m v_d}{2}\right) R_D$$

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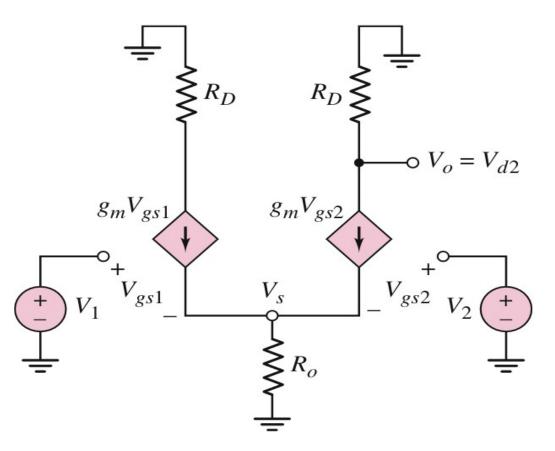
# Differential mode gain and input impedances

The differential voltage gain is

$$A_d = \frac{v_o}{v_d} = \frac{g_m R_D}{2} = \sqrt{\frac{K_n I_Q}{2}} \cdot R_D$$

- The differential and common-mode input impedances are:
  - We know that, at low frequencies, the input impedance of the MOSFET is infinite
  - Hence both the differential and common-mode input impedances are infinite too
  - As a design trade-off, sacrifice the differential mode gain.

# Small-Signal Equivalent Circuit: MOSFET Differential Amplifier



Assume that the transistors are matched, with  $\lambda$ =0 The output resistance of constant current source is finite,  $R_{o}$ 

The two transistors are biased with same quiescent current and

$$g_{m1} = g_{m2} \equiv g_m$$
.

## Refer Class notes

Writing a KCL equation at node  $V_s$ , we have

$$g_m V_{gs1} + g_m V_{gs2} = \frac{V_s}{R_o}$$

$$V_{gs1} = V_1 - V_s$$
 and  $V_{gs2} = V_2 - V_s$ 

$$g_m(V_1 + V_2 - 2V_s) = \frac{V_s}{R_o}$$

Solving for  $V_s$  we obtain

$$V_s = \frac{V_1 + V_2}{2 + \frac{1}{g_m R_o}}$$

For a one-sided output at the drain of  $M_2$ , we have

$$V_o = V_{d2} = -(g_m V_{gs2})R_D = -(g_m R_D)(V_2 - V_s)$$

$$V_{o} = -g_{m}R_{D} \left[ \frac{V_{2} \left( 1 + \frac{1}{g_{m}R_{o}} \right) - V_{1}}{2 + \frac{1}{g_{m}R_{o}}} \right]$$

$$V_o = \frac{g_m R_D}{2} V_d - \frac{g_m R_D}{1 + 2g_m R_o} V_{cm}$$

The output voltage, in general form, is

$$V_o = A_d V_d + A_{cm} V_{cm}$$

The transconductance  $g_m$  of the MOSFET is

$$g_m = 2\sqrt{K_n I_{DQ}} = \sqrt{2K_n I_Q}$$

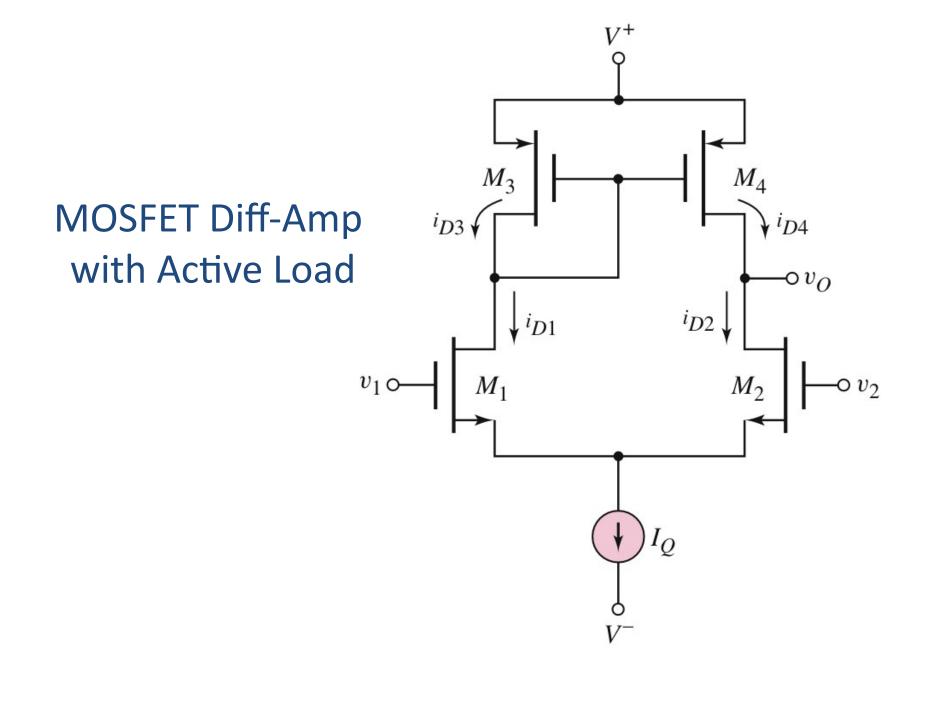
$$A_d = \frac{g_m R_D}{2} = \sqrt{2K_n I_Q} \left(\frac{R_D}{2}\right) = \sqrt{\frac{K_n I_Q}{2}} \cdot R_D$$

and the common-mode gain

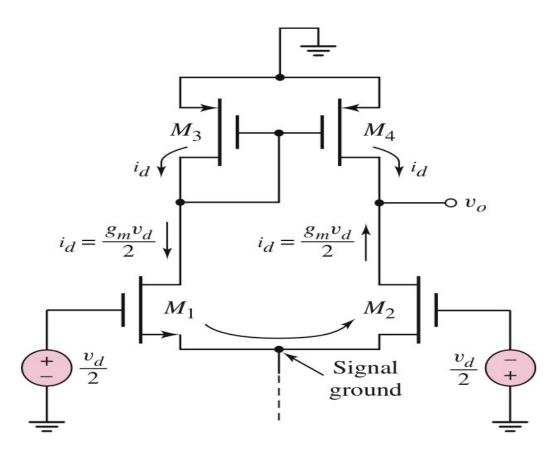
$$A_{cm} = \frac{-g_m R_D}{1 + 2g_m R_o} = \frac{-\sqrt{2K_n I_Q} \cdot R_D}{1 + 2\sqrt{2K_n I_Q} \cdot R_o}$$

$$CMRR = \frac{1}{2} \left[ 1 + 2\sqrt{2K_n I_Q} \cdot R_o \right]$$

## Refer class notes

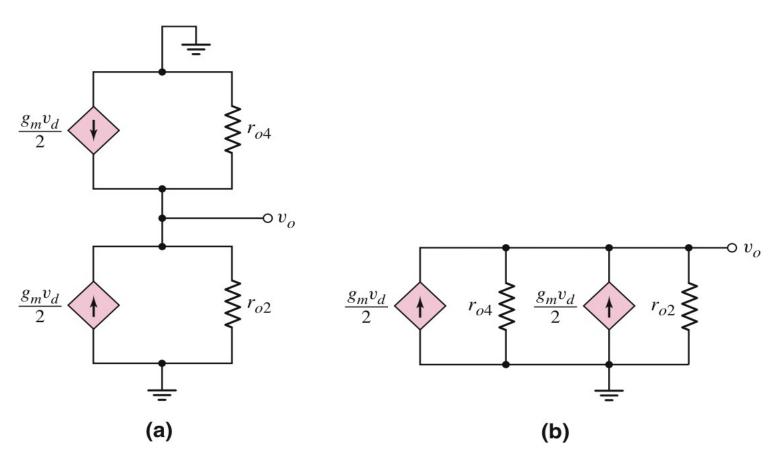


# AC Equivalent Circuit: MOSFET Diff-Amp with Active Load



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# Small-Signal Equivalent Circuit: MOSFET Diff-Amplifier with Active Load



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### Differential Mode Gain

$$v_o = 2\left(\frac{g_m v_d}{2}\right) (r_{o2} || r_{o4})$$

$$A_d = \frac{v_o}{v_d} = g_m(r_{o2} || r_{o4})$$

Equation (11.106) can be rewritten in the form

$$A_d = \frac{g_m}{\frac{1}{r_{o2}} + \frac{1}{r_{o4}}} = \frac{g_m}{g_{o2} + g_{o4}}$$

$$g_m = 2\sqrt{K_n I_D} = \sqrt{2K_n I_Q}, g_{o2} = \lambda_2 I_{DQ2} = (\lambda_2 I_Q)/2, g_{o4} = \lambda_4 I_{DQ4} = (\lambda_4 I_Q)/2$$
, then

$$A_d = \frac{2\sqrt{2K_nI_Q}}{I_Q(\lambda_2 + \lambda_4)} = 2\sqrt{\frac{2K_n}{I_Q}} \cdot \frac{1}{\lambda_2 + \lambda_4}$$